



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DESCRIPTION (CONTINUED)

The same internal circuit can also be used to provide a gate shaping signal of VGH for the LCD panel controlled by the signal applied to the CTRL input. For highest safety the TPS65150 has an integrated adjustable shutdown latch feature to allow application specific flexibility. The device monitors the outputs (Vs, VGL, VGH); and, as soon as one of the outputs falls below its power good threshold, the device enters shutdown latch, after its adjustable delay time has passed by.

ORDERING INFORMATION⁽¹⁾

T _A	ORDERING NUMBER	PACKAGE ⁽²⁾	PACKAGE MARKING
–40°C to 85°C	TPS65150PWP	TSSOP24 (PWP)	TPS65150
	TPS65150RGE	QFN-24 (RGE)	TPS65150

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.
 (2) The PWP package is available taped and reeled. Add R suffix to the device type (TPS65150PWPR) to order quantities of 2000 and (TPS65150RGER) to order quantities of 3000 devices per reel. Without suffix the device is shipped in tubes.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	UNIT
Voltages on pin VIN ⁽²⁾	–0.3 V to 7 V
Voltages on pin SUP	–0.3 V to 15.5 V
Voltage on pin SW	20 V
Voltage on CTRL	–0.3 V to 7 V
Voltage on GD	15.5 V
Voltage on CPI	32V
Continuous power dissipation	See Dissipation Rating Table
Operating junction temperature range	–40°C to 150°C
Storage temperature range	–65°C to 150°C
Lead temperature (soldering, 10 sec)	260°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
 (2) All voltage values are with respect to network ground terminal.

DISSIPATION RATINGS

PACKAGE	θ _{JA}	T _A ≤ 25°C POWER RATING	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
24 pin TSSOP	30.13 C°/W (PowerPad™ soldered)	3.3 W	1.83 W	1.32 W
24 pin QFN	30 C°/W (PowerPad™ soldered)	3.3 W	1.8 W	1.3 W

RECOMMENDED OPERATING CONDITIONS

	MIN	TYP	MAX	UNIT
VIN Input voltage range	1.8		6.0	V
V _S Output voltage range of the main boost converter V _S			15	V
L Inductor ⁽¹⁾		4.7		μH
T _A Operating ambient temperature	–40		85	°C

- (1) Refer to application section for further information.

RECOMMENDED OPERATING CONDITIONS (continued)

	MIN	TYP	MAX	UNIT
T _J Operating junction temperature	–40		125	°C

ELECTRICAL CHARACTERISTICS

V_{IN} = 3.3 V, V_S = 10 V, T_A = –40°C to 85°C, typical values are at T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT						
V _{IN}	Input voltage range		1.8		6.0	V
I _{QVIN}	No load quiescent current into Vin	Device is not switching		14	25	µA
I _{QSUP}	No load quiescent current into SUP	Device is not switching		1.9	3	mA
I _{QVCOM}	VCOM quiescent current into SUP			750	1500	µA
V _{UVLO}	Undervoltage lockout threshold	V _{IN} falling		1.6	1.8	V
V _{hys}	Undervoltage lockout threshold	V _{IN} rising		1.7	1.9	V
	Thermal shutdown	Temperature rising		155		°C
	Thermal shutdown hysteresis			10		°C
LOGIC SIGNALS CTRL						
V _{IH}	High level input voltage		1.6			V
V _{IL}	Low level input voltage				0.4	V
I _I	Input leakage current	CTRL=GND or VIN		0.01	0.2	µA
MAIN BOOST CONVERTER						
V _S	Output voltage range				15	V
V _{FB}	Feedback regulation voltage		1.136	1.146	1.154	V
I _{FB}	Feedback input bias current			10	100	nA
R _{DS(on)}	N-MOSFET on-resistance (Q1)	V _S = 10 V; I _{sw} = 500 mA		200	300	mΩ
		V _S = 5 V; I _{sw} = 500 mA		305	450	
	P-MOSFET on-resistance (Q2)	V _S = 10 V; I _{sw} = 500 mA		8	15	Ω
		V _S = 5 V; I _{sw} = 500 mA		12	22	
I _{MAX}	Maximum P-MOSFET peak switch current				1	A
I _{LIM}	N-MOSFET switch current limit (Q1)		2.0	2.5	3.4	A
I _{leak}	Switch leakage current	V _{sw} = 15 V		1	10	µA
V _{ovp}	Output overvoltage protection	V _{OUT} rising	16		20	V
f _{OSC}	Oscillator frequency		1.02	1.2	1.38	MHz
	Line regulation	V _{in} =1.8V to 5.0V, I _{load} =1mA		0.007		%/V
	Load regulation	V _{in} =5V, I _{load} =0A to 400mA		0.16		%/A
NEGATIVE CHARGE PUMP VGL						
V _G L	Output voltage range				–2	V
V _{REF}	Reference Voltage on pin REF		1.205	1.213	1.219	V
V _{FB}	Feedback regulation voltage		–36	0	36	mV
I _{FB}	Feedback input bias current			10	100	nA
R _{DS(on)}	Q4 P-Channel switch RDSON	I _{OUT} = 20 mA		4.4		Ω
V _{DropN}	Current sink voltage drop ⁽¹⁾	I _{DRN} = 50 mA, V _{FBN} = V _{FBNNominal} – 5%		130	300	mV
		I _{DRN} = 100 mA, V _{FBN} = V _{FBNNominal} – 5%		280	450	
	Load regulation	V _G L=–5V, I _{load} =0mA to 20mA		0.016		%/mA
POSITIVE CHARGE PUMP OUTPUT						
V _{CPO}	Output voltage range	CTRL = GND, V _{GH} = open			30	V

(1) The maximum charge pump output current is half the drive current of the internal current source or sink.

ELECTRICAL CHARACTERISTICS (continued)

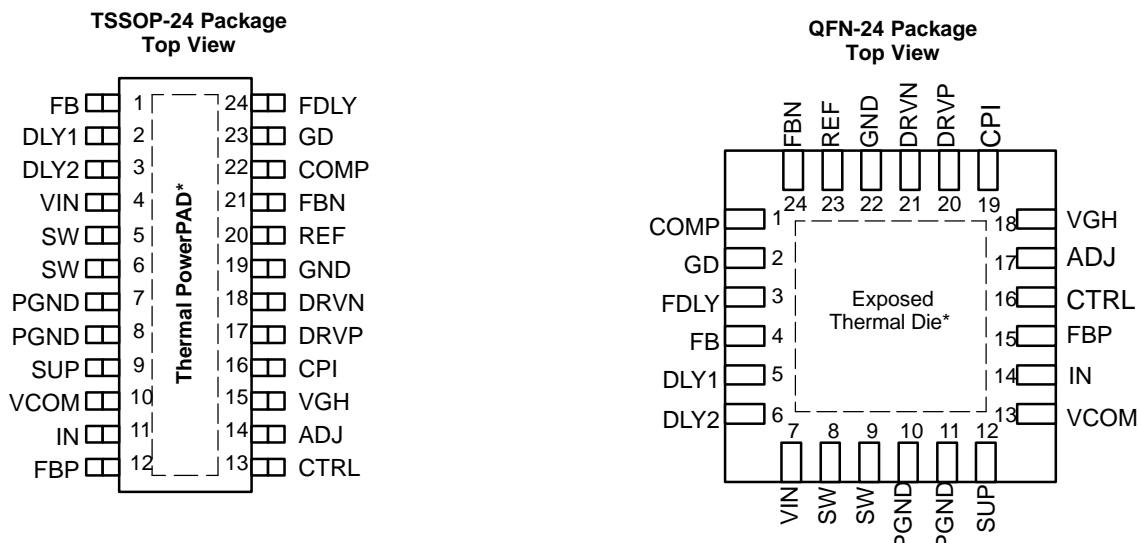
VIN = 3.3 V, VS = 10 V, TA = –40°C to 85°C, typical values are at TA = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{FB}	Feedback regulation voltage	CTRL = GND, V _{GH} = open	1.187	1.214	1.238	V
I _{FB}	Feedback input bias current	CTRL = GND, V _{GH} = open		10	100	nA
R _{DS(on)}	Q3 P-Channel switch R _{DSon}	I _{OUT} = 20 mA		1.1		Ω
V _{DropN}	Current sink voltage drop ⁽¹⁾	I _{DRP} = 50 mA, V _{FBP} = V _{FBPNominal} – 5%		420	650	mV
		I _{DRP} = 100 mA, V _{FBP} = V _{FBPNominal} – 5%		900	1400	
Load regulation		V _{GH} =24V, I _{load} =0mA to 20mA		0.07		%/mA
VGH ISOLATION SWITCH, GATE VOLTAGE FALL TIME CONTROL						
R _{DS(on)}	Q5 - Pass MOSFET R _{DSon}	I _{OUT} = 20 mA		12	30	Ω
I _{adj}	Capacitor charge current	V _{adj} = 20 V, C _{PI} = 30 V	160	200	240	μA
	Minimum output voltage	V _{adj} = 0 V, I _{VGH} = 10 mA		2		V
I _{VGH}	Maximum output current		20			mA
TIMING CIRCUITS DLY1, DLY2, FDLY						
I _{DLY1}	Drive current into delay capacitor DLY1	V _{DLY1} = 1.213 V	3	5	7	μA
I _{DLY2}	Drive current into delay capacitor DLY1	V _{DLY2} = 1.213 V	3	5	7	μA
R _{FDLY}	Fault time delay resistror ⁽²⁾		250	450	650	kΩ
GATE DRIVE (GD)						
V _(GD, Vs)	Gate drive threshold ⁽³⁾	V _s rising	–12% of V _s		–4% of V _s	V
V _{OL}	Gate drive output low voltage	I _(sink) = 500 μA			0.5	V
I _{LKG}	Gate drive output leakage current	V _{GD} = 15 V		0.001	1	μA
Vcom Buffer						
V _{CM}	Common mode input range		2.25	(V _s) –2V		V
V _{os}	Input offset voltage	I _{OUT} = 0 mA	–25		25	mV
	DC load regulation	I _o = ±25 mA	–37		37	mV
		I _o = ±50 mA	–77		55	
		I _o = ±100 mA	–85		85	
		I _o = ±150 mA	–110		110	
I _B	V _{COMIN} Input bias current		–300	–30	300	nA
I _{peak}	Peak output current	V _s = 15 V	1.2			A
		V _s = 10 V	0.65			
		V _s = 5 V	0.15			

(2) The fault time is calculated as: $t_F = C \times R = C \times 450 \text{ k}\Omega$

(3) The GD signal is latched low when the main boost converter output VS is within regulation. The GD signal is reset when the input voltage or enable of the boost converter is cycled low.

PIN ASSIGNMENT



* The thermal die (PowerPAD™) is connected to GND.

TERMINAL FUNCTIONS

TERMINAL		I/O	DESCRIPTION
NAME	NO.		
	QFN	TSSOP	
ADJ	17	14	I/O
COMP	1	22	O
CPI	19	16	I
CTRL	16	13	I
DLY1	5	2	I/O
DLY2	6	3	I/O
DRVN	21	18	I/O
DRVVP	20	17	I/O
FB	4	1	I
FBN	24	21	I
FBP	15	12	I
FDLY	3	24	I/O
GD	2	23	I
GND	22	19	Analog ground

TERMINAL FUNCTIONS (continued)

TERMINAL			I/O	DESCRIPTION
NAME	NO.			
	QFN	TSSOP		
IN	14	11	I	Input of the Vcom buffer. If this pin is connected to GND, the Vcom buffer is disabled.
PGND	10, 11	7, 8		Power ground
REF	23	20	O	Internal reference output typically 1.213 V
SUP	12	9	I/O	Supply pin of the positive, negative charge pump and Boost Converter Gate Drive Circuit. This pin needs to be connected to the output of the main boost converter and can't be connected to any other voltage rail.
SW	8, 9	5, 6	I	Switch pin of the boost converter
VGH	18	15	O	Positive output voltage to drive the TFT gates with an adjustable falltime. This pin is internally connected with a MOSFET switch to the positive charge pump input CPI.
VIN	7	4	I	This is the input voltage pin of the device.
VCOM	13	10	O	VCOM buffer output. Typically a 1-μF output capacitor is required on this pin.
PowerPAD™, exposed thermal die	NA	NA		The PowerPAD™ needs to be soldered to GND

TYPICAL CHARACTERISTICS

TABLE OF GRAPHS

			FIGURES
Main Boost Converter			
η	Efficiency	vs Load current $V_S=10\text{ V}$	1
η	Efficiency	vs Load current $V_S=13.5\text{ V}$	2
η	Efficiency	vs Load current $V_S=15\text{ V}$	3
f_{SW}	Switching frequency	vs Input voltage and temperature	4
	PWM operation	at nominal load current	5
	PWM operation	at light load current	6
	Load transient response		7
	Softstart boost converter		8
	Power-on sequencing		9
	Power-on sequencing	External MOSFET in series to V_S	10
	Gate voltage shaping of V_{GH}		11
	Adjustable Fault detection		12
Negative Charge Pump Driver			
V_{GL}	V_{GL}	vs load current	13
Positive Charge Pump Driver			
V_{GH}	V_{GH}	vs load current; Charge pump doubler stage	14
V_{GH}	V_{GH}	vs load current; Charge pump tripler stage	15
VCOM Buffer			
	VCOM Buffer transconductance		16

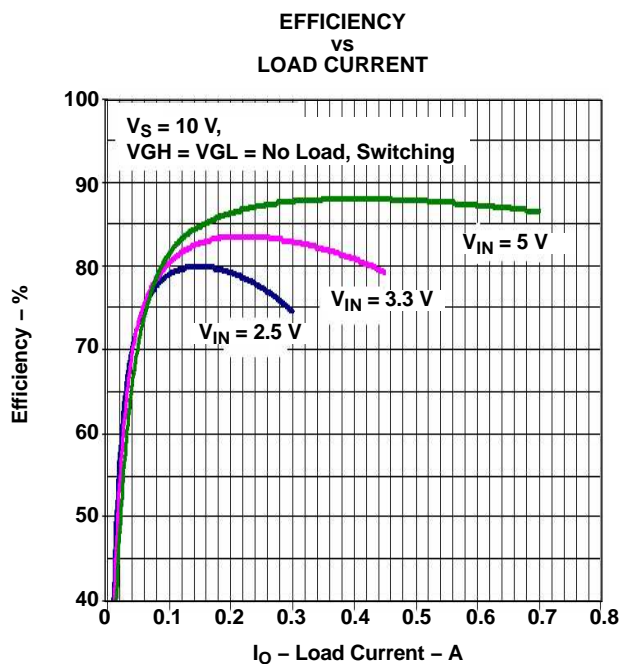


Figure 1.

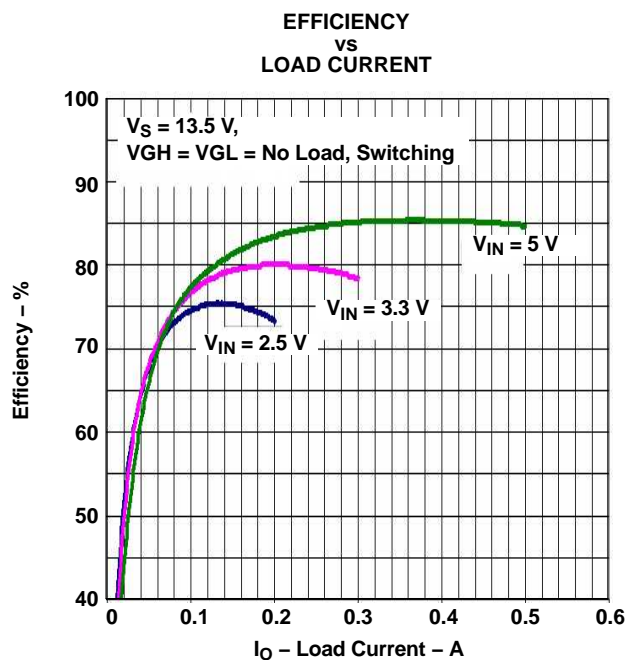


Figure 2.

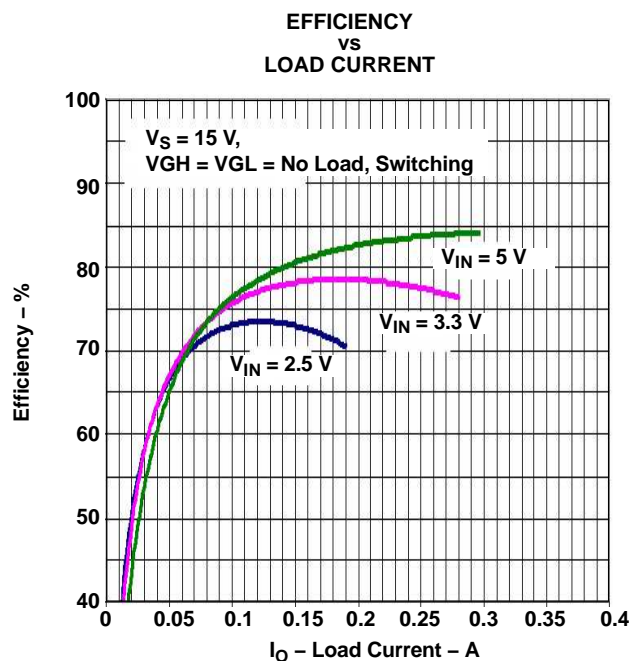


Figure 3.

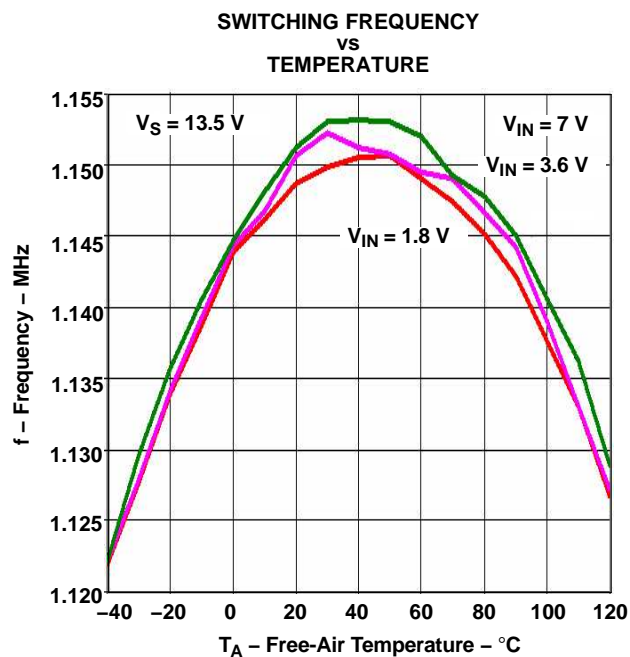


Figure 4.

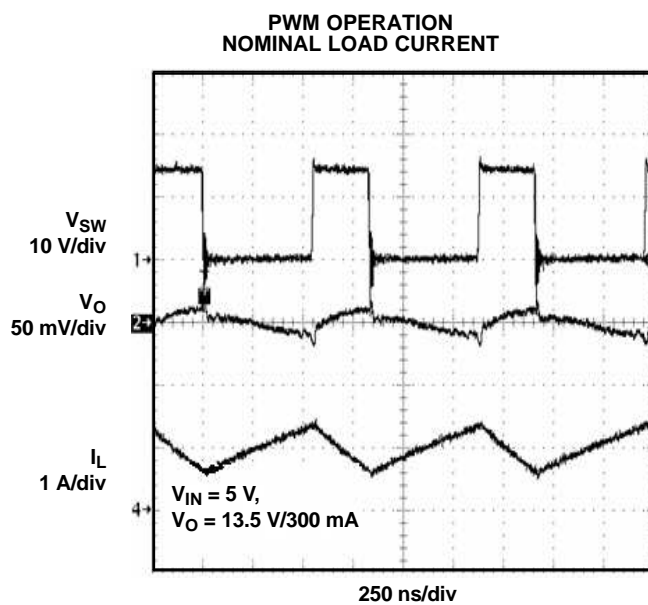


Figure 5.

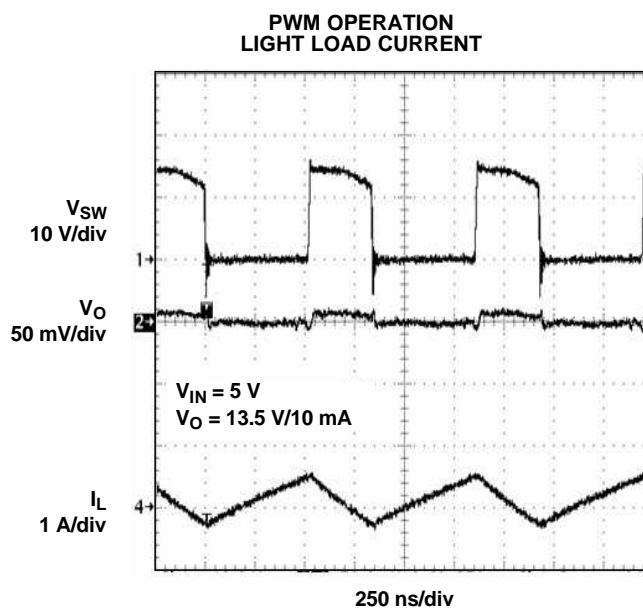


Figure 6.

LOAD TRANSIENT RESPONSE

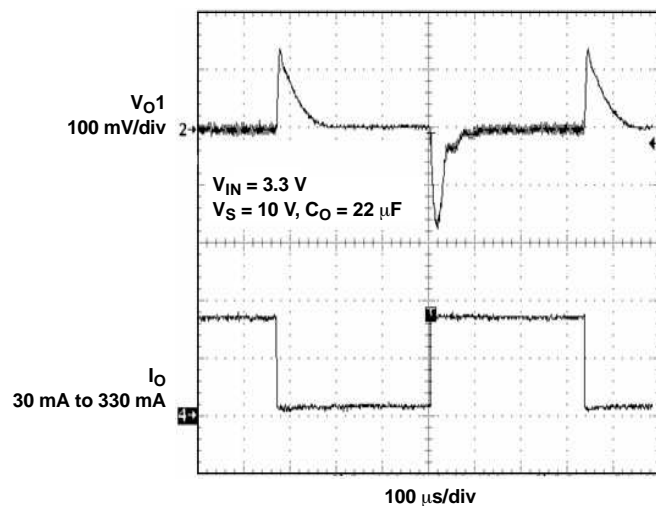


Figure 7.

SOFT START BOOST CONVERTER

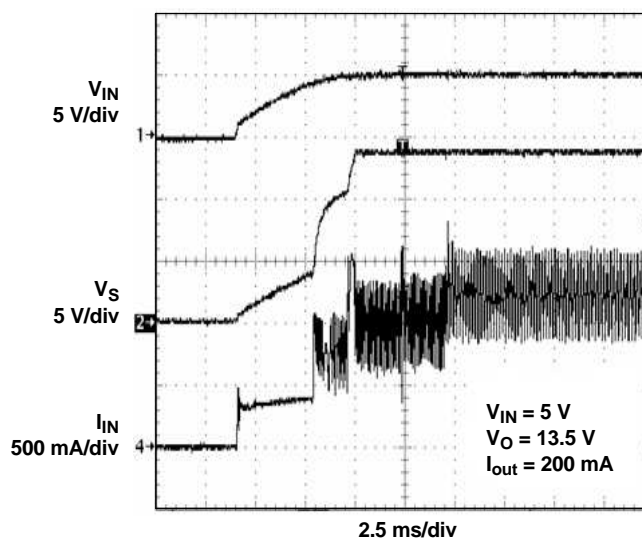


Figure 8.

POWER-ON SEQUENCING

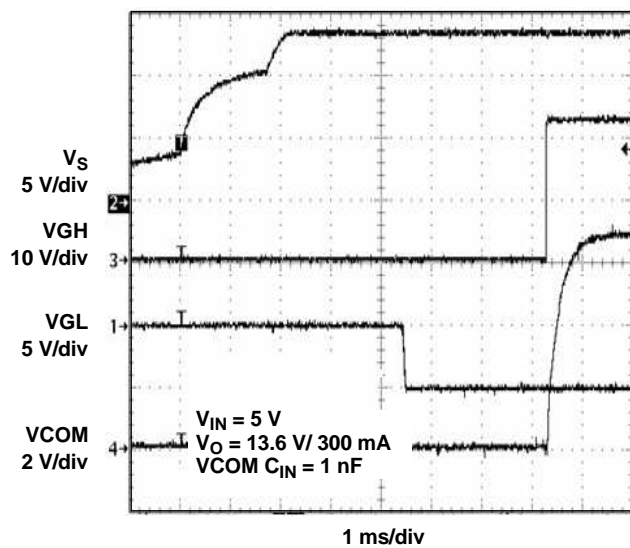


Figure 9.

POWER-ON SEQUENCING WITH EXTERNAL ISOLATION MOSFET AT V_S

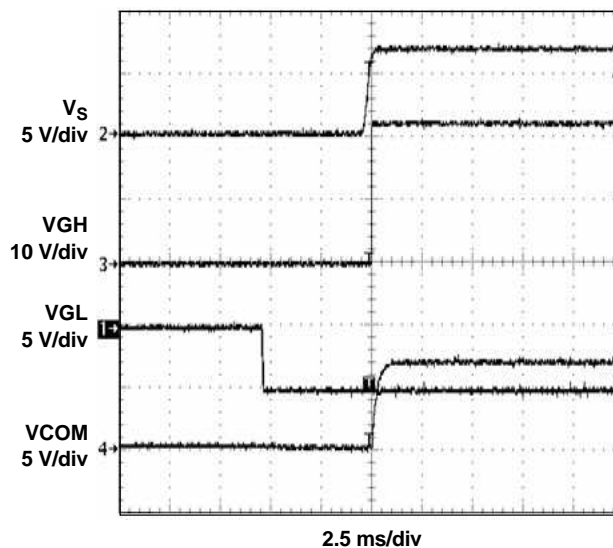


Figure 10.

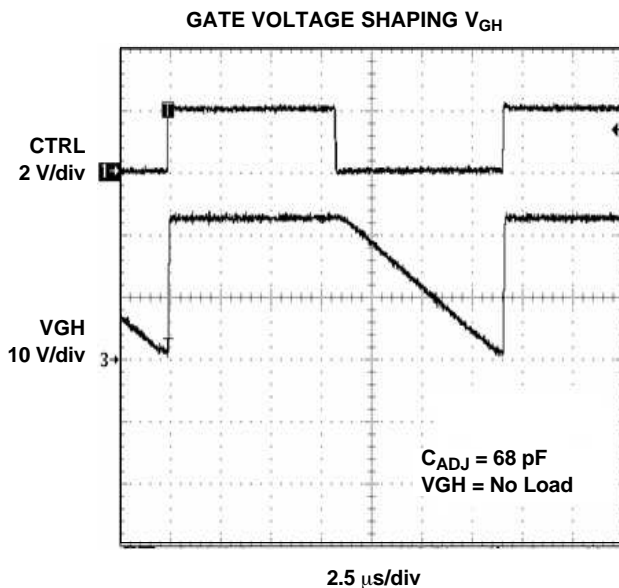


Figure 11.

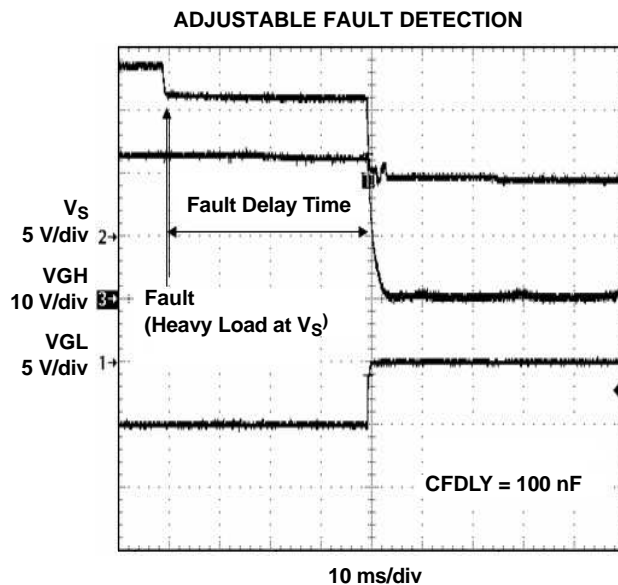


Figure 12.

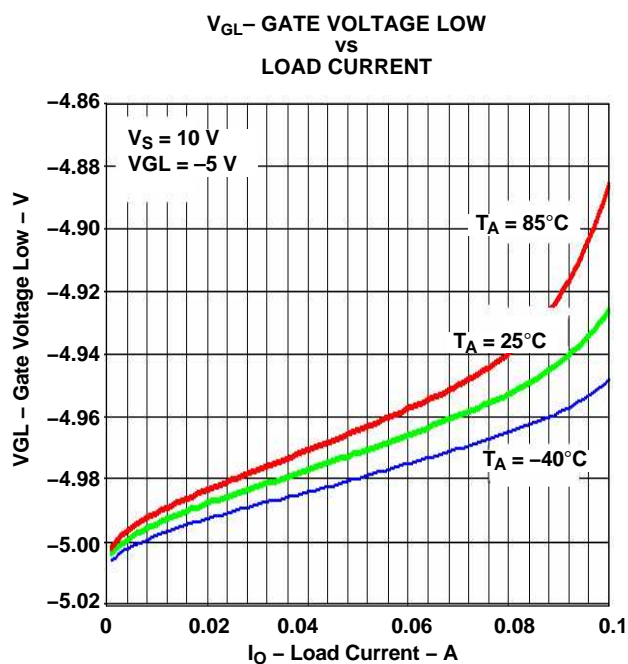


Figure 13.

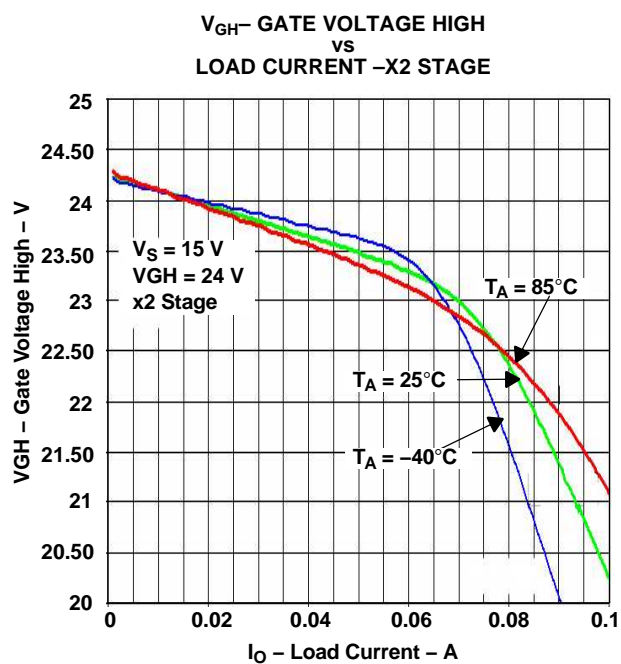


Figure 14.

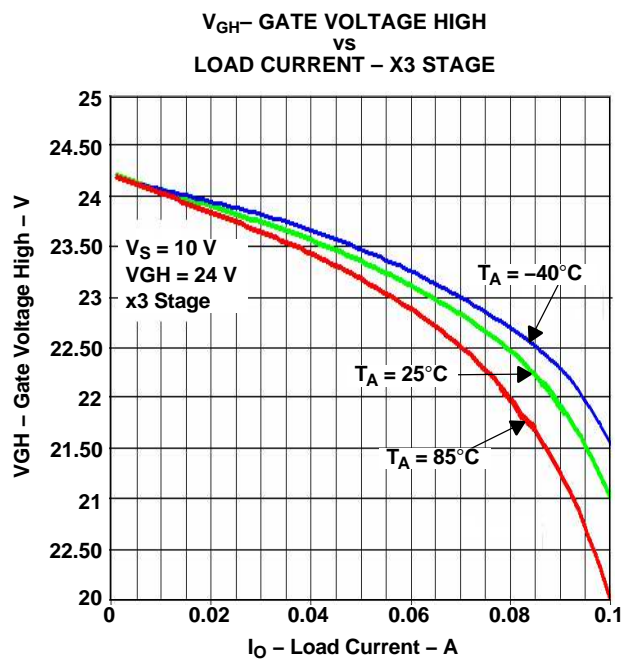


Figure 15.

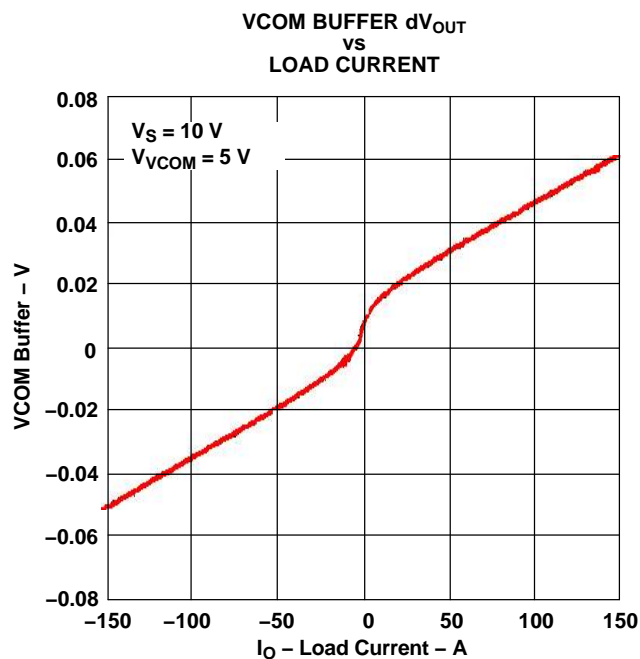
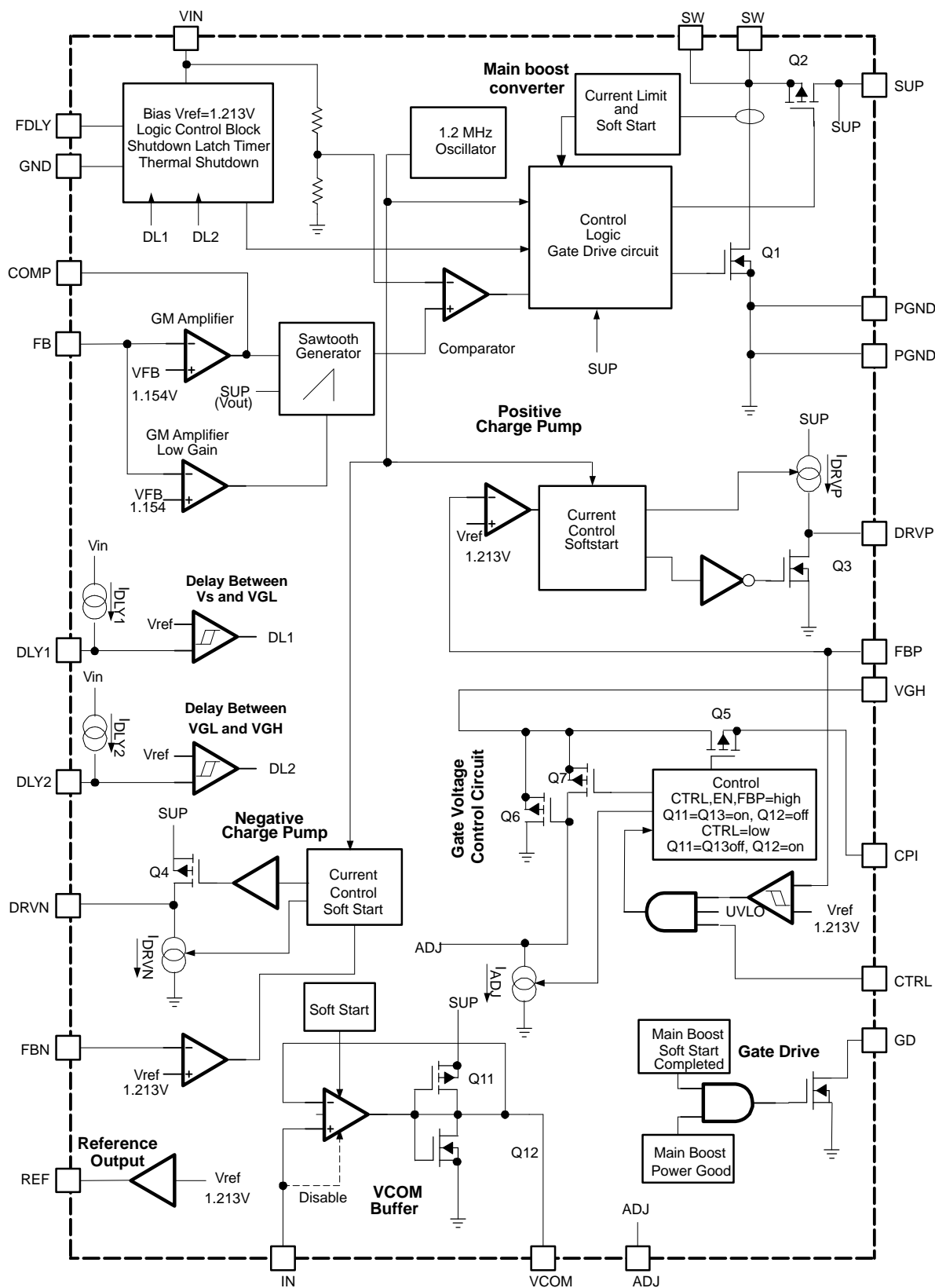


Figure 16.

FUNCTIONAL BLOCK DIAGRAM



DETAILED DESCRIPTION

Main Boost Converter

The main boost converter operates with pulse width modulation (PWM) and a fixed switching frequency of 1.2 MHz. The converter uses an unique fast response, voltage mode controller scheme with input voltage feedforward. This achieves excellent line and load regulation (0.16%/A load regulation typical) and allows the use of small external components. To add higher flexibility to the selection of external component values the device uses external loop compensation. Although the boost converter looks like a non-synchronous boost converter topology operating in discontinuous conduction mode at light load current the TPS65150 maintains continuous conduction even at light load currents. This is achieved by using the Virtual Synchronous Converter Technology having an external Schottky diode with an integrated MOSFET in parallel connected between SW pin and the SUP pin. See *Functional Block Diagram*. The intention of this MOSFET is to allow the current to go below ground which is the case at light load conditions. For this purpose a small integrated P-Channel MOSFET, with typically 10-Ω $R_{DS(on)}$, is sufficient. When the inductor current is positive the external Schottky diode with the lower forward voltage conducts the current. This causes the converter to operate with a fixed frequency in continuous conduction mode over the entire load current range. This avoids the ringing on the switch pin as seen with standard non-synchronous boost converter and allows a simpler compensation for the boost converter.

Soft Start

The main boost converter as well as the charge pump driver have an internal soft-start circuit. This avoids heavy voltage drops at the input voltage rail or at the output of the main boost converter V_S during startup caused by high inrush currents. As the main boost converter starts up the internal current limit threshold is increased in three steps. The device starts with the first step where the current limit is set to 2/5 of the typical current limit (2/5 of 2.3 A) for 2048 clock cycles then increased to 3/5 of the current limit for 2048 clock cycles and the 3rd step is the full current limit. This gives a typical start-up time around 5 ms.

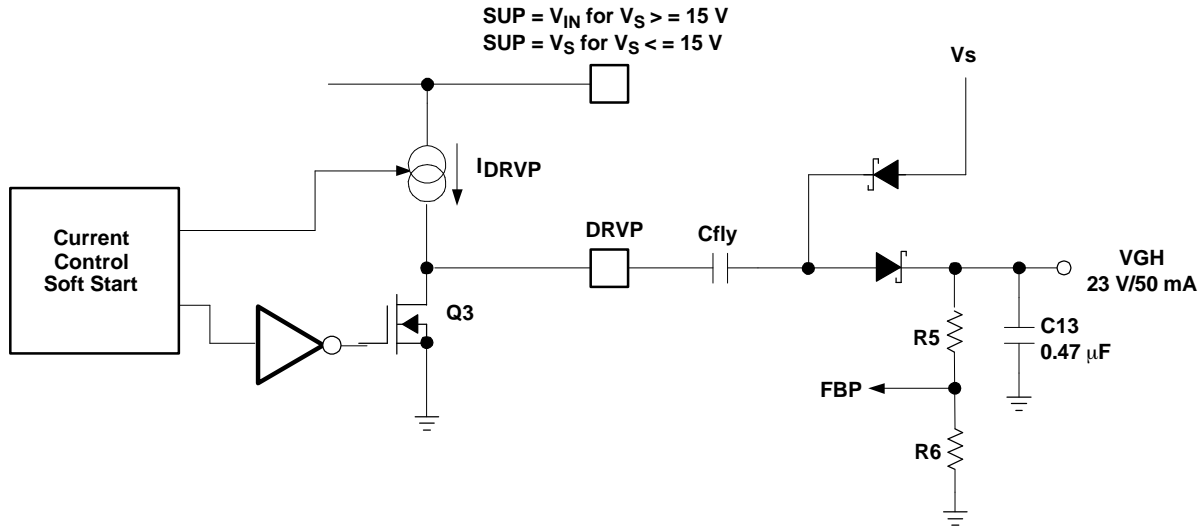
Adjustable Fault Delay

The TPS65150 has an adjustable delay timer integrated shutting down the entire device in case of a fault at the outputs. The fault timer is also active during startup. Connecting a capacitor from the FDLY pin to V_{in} sets the delay time, from the point where one of the outputs (V_S , V_{GH} , V_{GL}) drops below its power good threshold, until the device enters the shutdown latch. Since the fault delay timer is also active during startup, the device enters shutdown when the output voltage of the main boost converter, V_S , does not reach its power-good threshold after the fault delay time has passed. When an external isolation switch is used, shown in Figure 24, then the device provides short circuit protection even during start-up. To restart the device, the input voltage has to be cycled to GND. The shutdown function can be disabled by connecting FDLY to V_{IN} . The fault delay time is calculated as:

$$t_F = C \times R = C \times 450 \text{ k}\Omega = 100 \text{ nF} \times 450 \text{ k}\Omega \approx 40 \text{ ms}$$

Positive Charge Pump

The positive charge pump provides a regulated output voltage, set by the external resistor divider. [Figure 17](#) shows an extract of the positive charge pump driver circuit out of the block diagram. The operation of the charge pump driver can be understood best by looking at [Figure 17](#). During the first cycle Q3 is turned on and the flying capacitor, C_{fly} , is charged to the source voltage, V_S . During the next clock cycle Q3 is turned off, and the current source charges the drive pin, DRVP, up to the supply voltage, V_{SUP} . Since the flying capacitor voltage sits on top of the drive pin voltage the maximum output voltage is $V_{GH} = V_{sup} + V_S - V_{drop}$. V_{drop} is the voltage drop across the external diodes and internal charge pump MOSFETs.

DETAILED DESCRIPTION (continued)**Figure 17. Extract of the Positive Charge Pump Driver**

If higher output voltages are required another charge pump stage can be added to the output, as shown in Figure 21 at the end of the data sheet. To minimize quiescent current a high impedance feedback divider should be used. The top feedback resistor should not be selected larger than 1MΩ.

Setting the output voltage:

$$V_{out} = 1.213 \times \left(1 + \frac{R5}{R6}\right)$$

$$R5 = R6 \times \left(\frac{V_{out}}{V_{FB}} - 1\right) = R6 \times \left(\frac{V_{out}}{1.213} - 1\right) \quad (1)$$

Negative Charge Pump

The negative charge pump provides a regulated output voltage set by the external resistor divider. The negative charge pump operates very similar to the positive charge pump with the difference that the voltage on the supply pin SUP is inverted. The maximum output voltage for a single stage charge pump inverter is $V_{GL} = (-V_{SUP}) + V_{drop}$. V_{drop} is the voltage drop across the external diodes and internal charge pump MOSFETs.

Setting the output voltage:

$$V_{out} = -V_{REF} \times \frac{R3}{R4} = -1.213 \text{ V} \times \frac{R3}{R4}$$

$$R3 = R4 \times \frac{|V_{out}|}{V_{REF}} = R4 \times \frac{|V_{out}|}{1.213} \quad (2)$$

The lower feedback resistor value, R4, should range between 40 kΩ to 120 kΩ; or, the overall feedback resistance should be within 500 kΩ to 1 MΩ. Smaller values load the reference too heavily; and larger values may cause stability problems. The negative charge pump requires two external Schottky diodes. The peak current rating of the Schottky diode has to be twice the load current of the output. For a 20-mA output current, the BAT54 dual Schottky diode is a good choice.

DETAILED DESCRIPTION (continued)

Power-on Sequencing, DLY1, DLY2

As soon as the input voltage is applied, and rises above the undervoltage lockout (UVLO), the device starts with the main boost converter, V_S , coming up first. Then the negative voltage, V_{GL} , comes up, set by the delay time DLY1; and then the positive charge pump, V_{GH} , set by the delay time DLY2. Finally, the V_{COM} buffer starts up. The delay times, DLY1 and DLY2, are set by the capacitor value connected to these pins. An internal current source charges the capacitor with a constant current of typically 5 μA until the voltage reaches the internal comparator trip point of $V_{ref} = 1.213 V$.

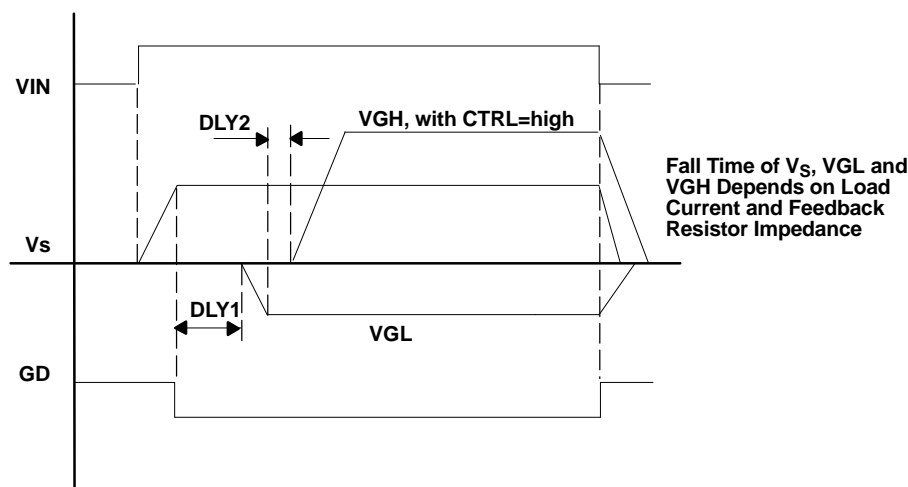


Figure 18. Power on Sequencing With CTRL = High

Setting the Delay Times DLY1, DLY2

Connecting an external capacitor to the DLY1 and DLY2 pins sets the delay time. If no delay time is required, these pins can be left open. To set the delay time, the external capacitor connected to DLY1 and DLY2 is charged with a constant current source of typically 5 μA . The delay time is terminated when the capacitor voltage has reached the internal reference voltage of $V_{ref} = 1.213 V$. The external delay capacitor is calculated:

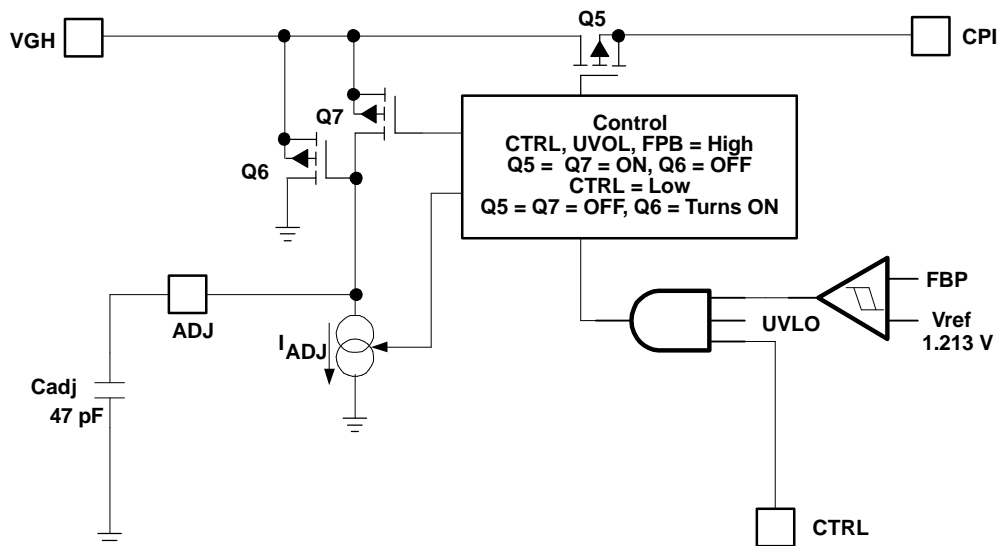
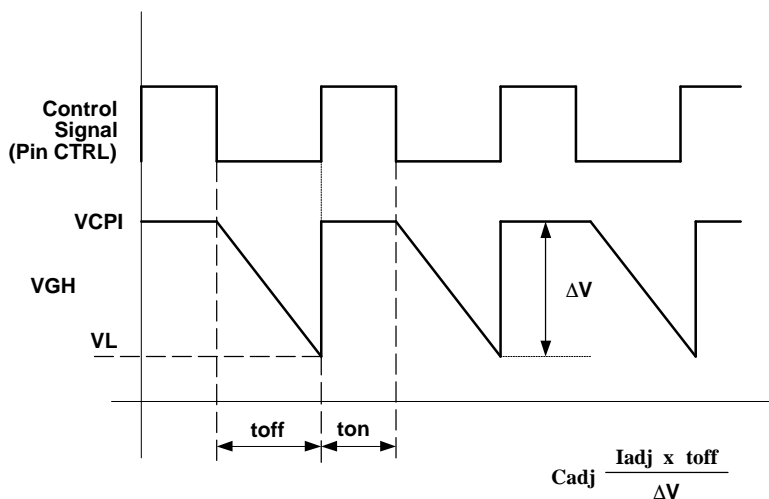
$$C_{dly} = \frac{5 \mu A \times t_d}{V_{REF}} = \frac{5 \mu A \times t_d}{1.213 V} \quad \text{with } t_d = \text{Desired delay time} \quad (3)$$

Gate Drive, GD

The gate drive pin can be used to drive an external MOSFET, providing isolation for the main boost converter V_S . The gate drive is an open drain output capable of sinking typically 500 μA . The gate drive is latched low as soon as the main boost converter, V_S , reaches its power-good threshold. The gate drive signal goes high impedance when the input voltage falls below the undervoltage lockout (UVLO) or the device enters shutdown latch triggered by the fault delay.

VGH Switch / Gate Voltage Shaping, CPI – VGH

The gate voltage shaping circuit is used to reduce crosstalk between the LCD pixels by adjusting the fall time of the positive gate voltage, V_{GH} . The CTRL pin needs to be connected to V_{in} if the gate voltage shaping function is not used. This function is implemented by adjusting the fall time of the gate voltage signal, V_{GH} , generated by the positive charge pump. The fall time can be adjusted with the external capacitor, C_{adj} connected to the ADJ pin. The corresponding timing diagram is shown in [Figure 20](#).

DETAILED DESCRIPTION (continued)**Figure 19. Implementation of the Gate voltage shaping****Figure 20. Timing Diagram of the Gate voltage shaping**

The control signal applied to CTRL sets the timing of VGH. When CTRL is high, Q5 is turned on and the positive charge pump voltage applied on CPI is present on VGH. At the same time, the capacitor connected to ADJ is charged up by Q7 to VGH, while Q6 is turned off. When CTRL is taken low, Q5 and Q7 turn off, and Q6 is slowly turned on as the capacitor on ADJ is discharged by the discharge current I_{ADJ} , typically 200 μA . The capacitor value on C_{ADJ} determines the fall time of VGH. For a given off time (toff), external capacitor Cadj determines the desired voltage drop, ΔV .

$$C_{adj} = \frac{I_{adj} \times t_{off}}{\Delta V} \quad \text{with } I_{adj} = 200 \mu\text{A} \quad (4)$$

When the input voltage falls below the undervoltage threshold (UVLO) or the device enters shutdown latch triggered by the fault delay timer, then VGH is disconnected from CPI by Q5 and is high impedance.

DETAILED DESCRIPTION (continued)

Thermal Shutdown

A thermal shutdown is implemented to prevent damage because of excessive heat and power dissipation. Typically, the thermal shutdown threshold is 155°C. When this threshold is reached, the device enters shutdown. The device can be enabled again by cycling the input voltage to GND.

Vcom Buffer

The VCOM Buffer is a transconductance amplifier designed to drive capacitive loads. The IN pin is the input of the VCOM buffer. If the VCOM buffer is not required for certain applications, it is possible to shut down the VCOM buffer by connecting IN to ground, reducing the overall quiescent current. The VCOM buffer features a soft start, avoiding a large voltage drop at Vs during startup. The VCOM buffer input, IN, cannot be pulled dynamically to ground during operation.

Boost Converter Design Procedure

The first step in the design procedure is to verify whether the maximum possible output current of the boost converter supports the specific application requirements. A simple approach is to estimate the converter efficiency, by taking the efficiency numbers from the provided efficiency curves, or use a worst case assumption for the expected efficiency, e.g. 75%.

$$1. \text{ Duty Cycle : } D = 1 - \frac{V_{in} \times \eta}{V_{out}} \quad (5)$$

$$2. \text{ Maximum output current : } I_{out} = \left(I_{sw} - \frac{V_{in} \times D}{2 \times f_s \times L} \right) \times (1 - D) \quad (6)$$

$$3. \text{ Peak switch current : } I_{swpeak} = \frac{V_{in} \times D}{2 \times f_s \times L} + \frac{I_{out}}{1 - D} \quad (7)$$

With

I_{sw} = Converter switch current (minimum switch current limit = 2.0 A)

f_s = Converter switching frequency (typical 1.2 MHz)

L = Selected inductor value

η = Estimated converter efficiency (use the number from the efficiency plots, or 0.75 as an estimation)

The peak switch current is the steady-state peak switch current that the integrated switch, inductor, and external Schottky diode has to be able to handle. The calculation must be done for the minimum input voltage where the peak switch current is highest. For the calculation of the maximum current delivered by the boost converter it needs to be considered that the positive and negative charge pumps as well as the VCOM buffer run from the output of the boost converter as well.

Inductor Selection

Several inductors work with the TPS65150. Especially with external compensation, the performance can be adjusted to the specific application requirements. The main parameter for the inductor selection is the inductor saturation current, which should be higher than the peak switch current as calculated previously with additional margin to cover for heavy load transients. The alternative, more conservative approach, is to choose the inductor with a saturation current at least as high as the typical switch current limit of 2.5 A. The second important parameter is the inductor DC resistance. Usually the lower the DC resistance the higher the efficiency. It is important to note that the inductor DC resistance is not the only parameter determining the efficiency. For a boost converter, where the inductor is the energy storage element, the type and material of the inductor influences the efficiency as well. Especially at high switching frequencies of 1.2 MHz, inductor core losses, proximity effects, and skin effects become more important. Usually an inductor with a larger form factor gives higher efficiency. The efficiency difference between different inductors can vary between 2% to 10%. For the TPS65150, inductor values between 3.3 μ H and 6.8 μ H are a good choice, but other values can be used as well. Possible inductors are shown in [Table 1](#).

DETAILED DESCRIPTION (continued)**Table 1. Inductor Selection**

INDUCTOR VALUE	COMPONENT SUPPLIER	DIMENSIONS IN mm	Isat – DC Resistance
4.7 µH	Coilcraft DO1813P-472HC	8,89 × 6,1 × 5,0	2.6 A – 54 mΩ
4.2 µH	Sumida CDRH5D28 4R2	5,7 × 5,7 × 3	2.2 A – 23 mΩ
4.7 µH	Sumida CDC5D23 4R7	6 × 6 × 2,5	1.6 A – 48 mΩ
4.2 µH	Sumida CDRH6D12 4R2	6,5 × 6,5 × 1,5	1.8 A – 60 mΩ
3.9 µH	Sumida CDRH6D28 3R9	7,0 × 7,0 × 3,0	2.6 A – 20 mΩ
3.3 µH	Sumida CDRH6D12 4R2	6,5 × 6,5 × 1,5	1.9 A – 50 mΩ

Output Capacitor Selection

For best output voltage filtering, a low ESR output capacitor is recommended. Ceramic capacitors have a low ESR value, but tantalum capacitors can be used as well, depending on the application. A 22-µF ceramic output capacitor works for most applications. Higher capacitor values can be used to improve the load transient regulation. See [Table 2](#) for the selection of the output capacitor.

Input Capacitor Selection

For good input voltage filtering, low ESR ceramic capacitors are recommended. A 22-µF ceramic input capacitor is sufficient for most applications. For better input voltage filtering, this value can be increased. See [Table 2](#), and *Typical Applications* for input capacitor recommendations.

Table 2. Input and Output Capacitor Selection

CAPACITOR	VOLTAGE RATING	COMPONENT SUPPLIER	COMMENTS
22 µF/1206	16 V	Taiyo Yuden EMK325BY226MM	Cout
22 µF/1206	6.3 V	Taiyo Yuden JMK316BJ226	Cin

Rectifier Diode Selection

To achieve high efficiency, a Schottky diode should be used. The reverse voltage rating should be higher than the maximum output voltage of the converter. The required average rectified forward current rating of the Schottky diode is calculated as the off time of the converter times the maximum switch current of the TPS65150:

$$D = 1 - \frac{V_{in}}{V_{out}} \quad (8)$$

$$I_{avg} = (1 - D) \times I_{sw} = \frac{V_{in}}{V_{out}} \times 2.0 \text{ A with } I_{sw} = \text{minimum switch current of the TPS65150 (2.0 A)} \quad (9)$$

Usually, a Schottky diode with 1-A maximum average rectified forward current rating is sufficient for most of the applications. Secondly, the Schottky rectifier has to be able to dissipate the power. The dissipated power is the average rectified forward current times the diode forward voltage.

$$PD = I_{avg} \times VF = I_{sw} \times (1 - D) \times VF \text{ with } I_{sw} = \text{minimum switch current of the TPS65150 (2.0 A).}$$

Typically, the diode should be able to dissipate 270 mW maximum depending on the load current and forward voltage. In terms of efficiency, the main parameters of the diode are the forward voltage and the reverse leakage current of the diode; both should be as low as possible.

Table 3. Rectifier Diode Selection

CURRENT RATING I_{avg}	Vr	V _{forward}	COMPONENT SUPPLIER
2 A	20 V	0.44 V at 2 A	SL22, Vishay Semiconductor
2 A	20 V	0.5 V at 2 A	SS22, Fairchild Semiconductor
1 A	30 V	0.44 V at 2 A	MBRS130L, Fairchild Semiconductor
1 A	20 V	0.45 V at 1 A	UPS120, Microsemi
1 A	20 V	0.45 V at 1 A	MBRM120, ON Semiconductor

Setting the Output Voltage

The output voltage is set by the external resistor divider and is calculated as:

$$V_{\text{out}} = 1.146 \text{ V} \times \left(1 + \frac{R_1}{R_2}\right) \quad (10)$$

To minimize quiescent current high impedance feedback resistors should be used. The upper feedback resistor R1 should not be larger than 1MΩ. Across the upper resistor, a bypass capacitor is required to speed up the circuit during load transients. The capacitor value is selected according to Table 4 and the formula (12) as shown in the next section.

Compensation (COMP) and feedforward capacitor

The regulator loop can be compensated by adjusting the external components connected to the COMP pin. The COMP pin is the output of the internal transconductance error amplifier. The compensation capacitor adjusts the low-frequency gain. Adding a resistor in series to it will increase the high frequency gain. Since the converter gain changes with the input voltage different compensation capacitors are required. Lower input voltages require a higher gain, and therefore a smaller compensation capacitor value.

Table 4. Compensation Components for different V_{IN} Voltages

V _{IN}	C _{COMP}	R _{COMP}	f _z
2.5 V	470 pF	68 kΩ	8.8 kHz
3.3 V	470 pF	33 kΩ	7.8 kHz
5.0 V	2.2 nF	0 kΩ	11.2 kHz

The feedforward capacitor across the feedback resistor divider of the boost converter sets an additional zero at the frequency f_z to compensate the loop. Typical values for f_z are shown in Table 4 giving a feedforward capacitor value as calculated below.

$$C_{\text{FF}} = \frac{1}{2 \times \pi \times f_z \times R_1} = \frac{1}{2 \times \pi \times 8.8 \text{ kHz} \times R_1} \quad (11)$$

Please refer to the typical application circuits at the end of the datasheet for detailed circuit configurations and values.

Layout Consideration

The PCB layout is an important step in the power supply design. An incorrect layout could cause converter instability, load regulation problems, noise, and EMI issues. Especially with a switching dc-dc converter at high load currents, too-thin PCB traces can cause significant voltage spikes. Good grounding becomes important as well. If possible, a common ground plane to minimize ground shifts between analog (GND) and power ground (PGND) is recommended. Additionally, the following PCB design layout guidelines are recommended for the TPS65150:

1. Boost converter output capacitor, input capacitor and Power ground (PGND) should form a star ground or should be directly connected together on a common power ground plane.
2. Place the input capacitor directly from the input pin (VIN) to ground.
3. Use a bold PCB trace to connect SUP to the output Vs.
4. Place a small bypass capacitor from the SUP pin to ground.
5. Use short traces for the charge-pump drive pins (DRVN, DRVP) of VGH and VGL because these traces carry switching currents.
6. Place the charge pump flying capacitors as close as possible to the DRVP and DRVN pin, avoiding a high voltage spikes at these pins.
7. Place the Schottky diodes as close as possible to the IC, respectively to the flying capacitors connected to DRVP and DRVN.
8. Carefully route the charge pump traces to avoid interference with other circuits since they carry high voltage switching currents.
9. Place the output capacitor of the VCOM buffer as close as possible to the output pin (VCOM).

10. The power pad of the TSSOP package needs to be soldered to the PCB for improved thermal performance.
11. The thermal pad of the QFN package needs to be soldered to the PCB for reliability and thermal performance reasons.

APPLICATION INFORMATION

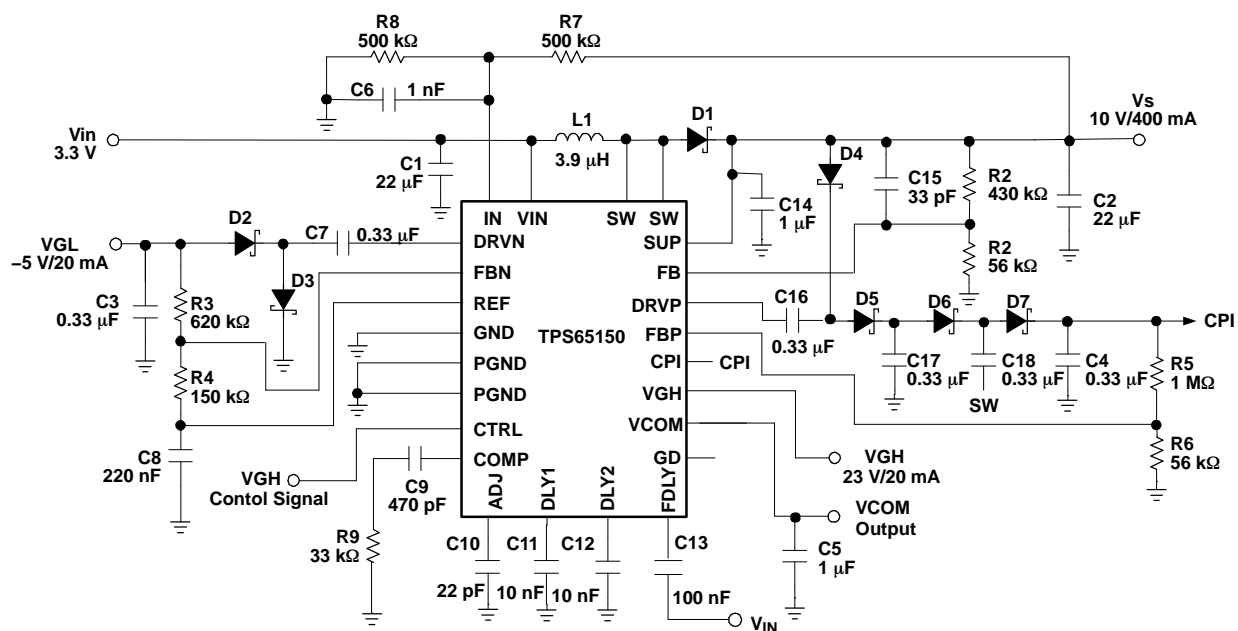


Figure 21. Notebook LCD Supply powered from a 3.3V rail

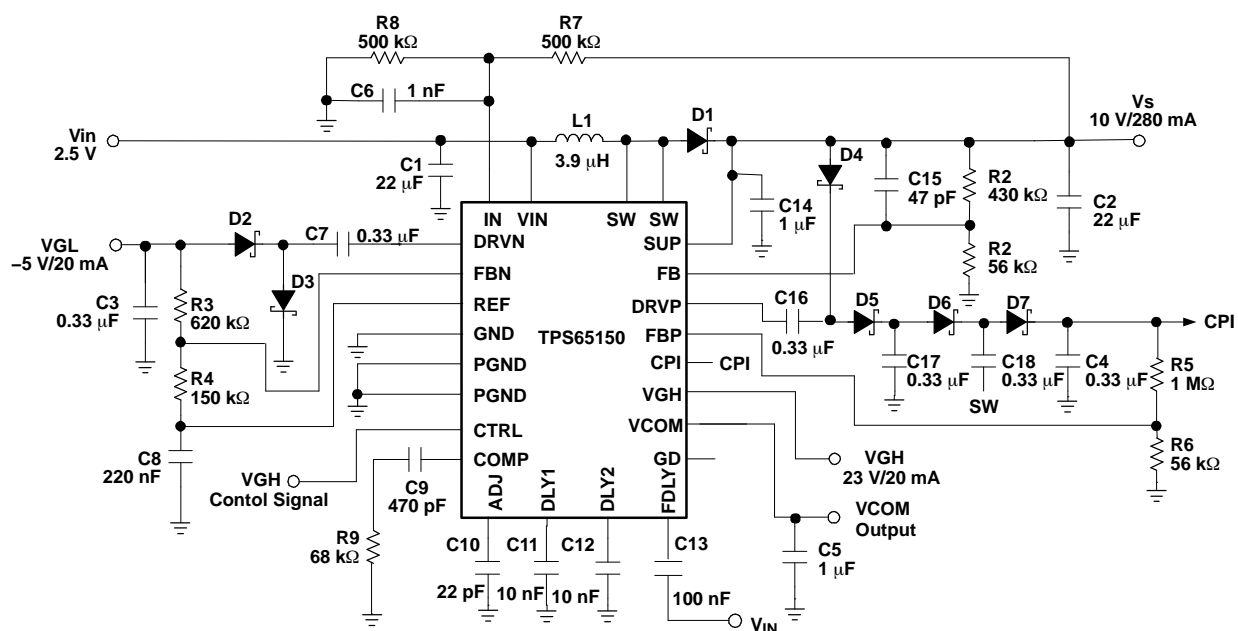
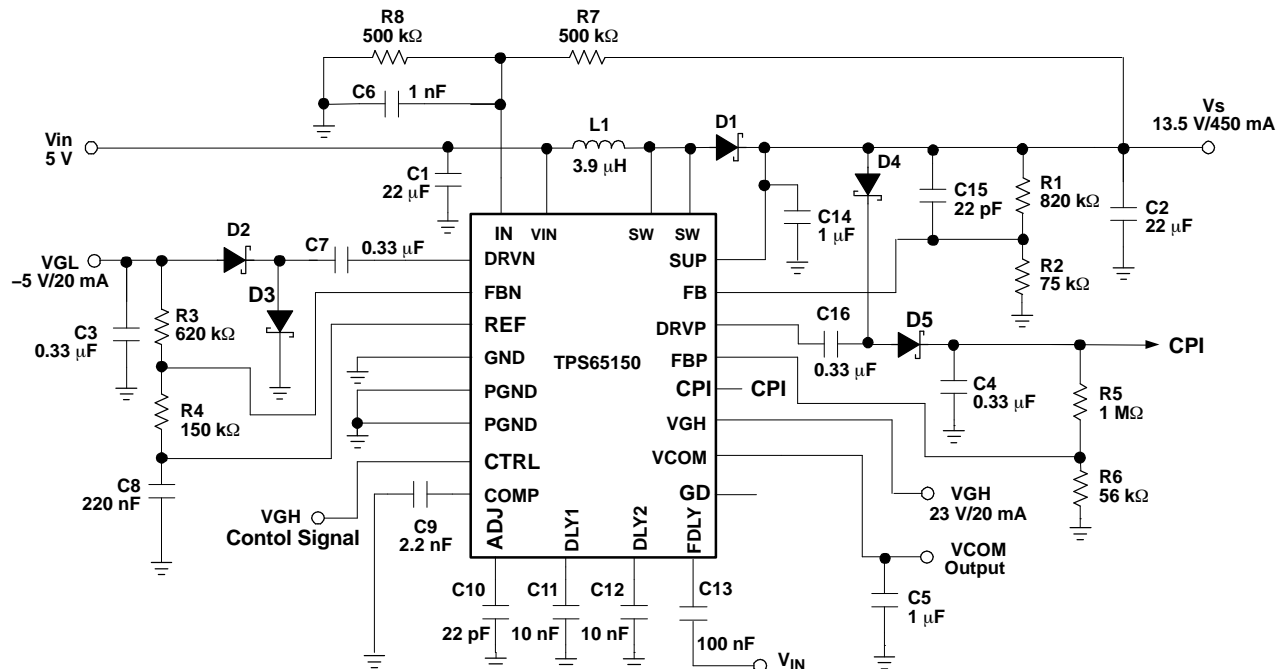
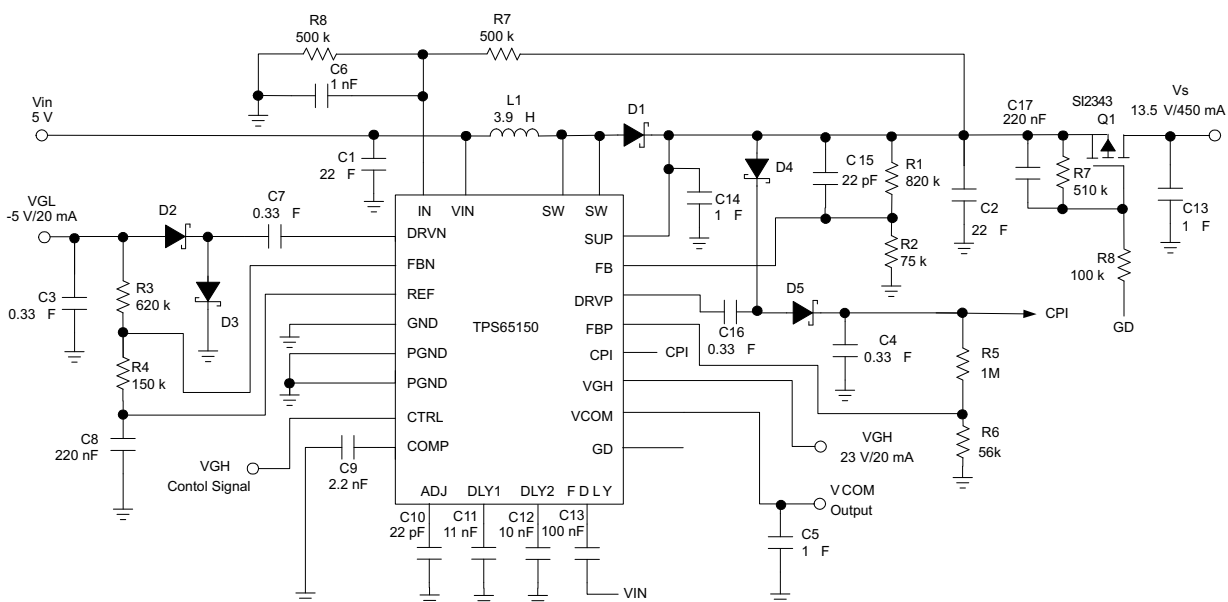


Figure 22. Notebook LCD Supply powered from a 2.5V rail

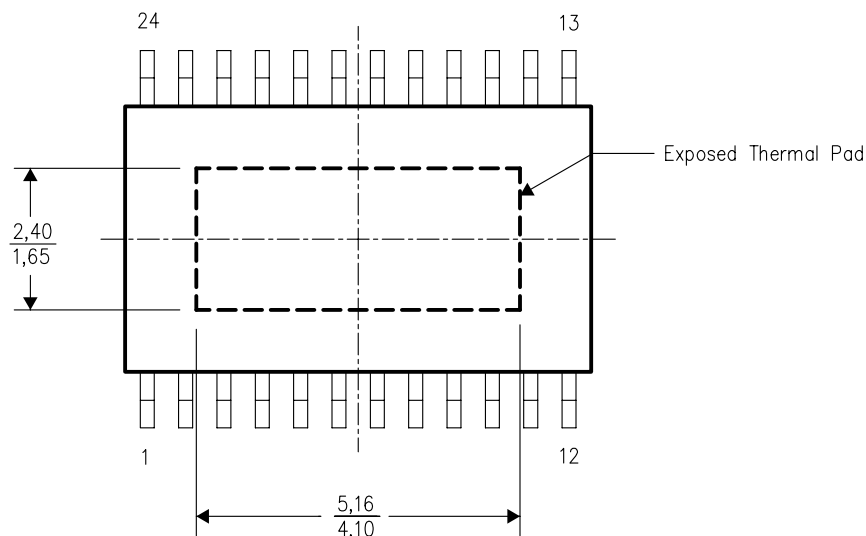
APPLICATION INFORMATION (continued)**Figure 23. Monitor LCD Supply powered from a 5V rail****Figure 24. Typical Isolation and Short-Circuit Protection Switch for Vs using Q1 and Gate Drive Signal (GD)**

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. When the thermal pad is soldered directly to the printed circuit board (PCB), the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to a ground plane or special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Top View

NOTE: All linear dimensions are in millimeters

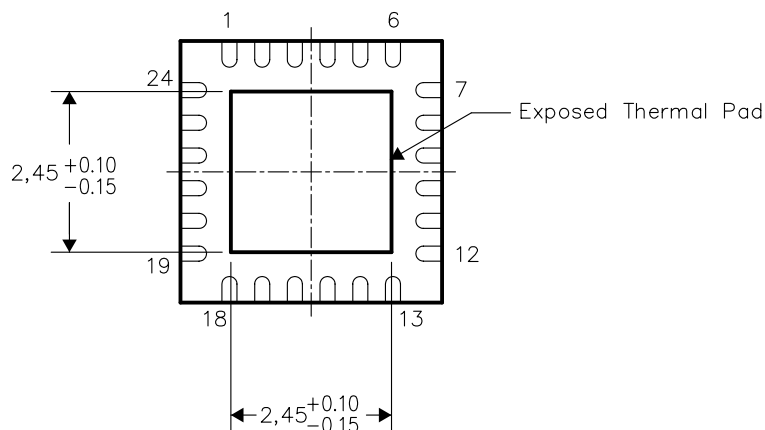
Exposed Thermal Pad Dimensions

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB), the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to a ground plane or special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No-Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPS65150PWP	ACTIVE	HTSSOP	PWP	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS65150PWPG4	ACTIVE	HTSSOP	PWP	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS65150PWPR	ACTIVE	HTSSOP	PWP	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS65150PWPRG4	ACTIVE	HTSSOP	PWP	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS65150RGER	ACTIVE	QFN	RGE	24	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

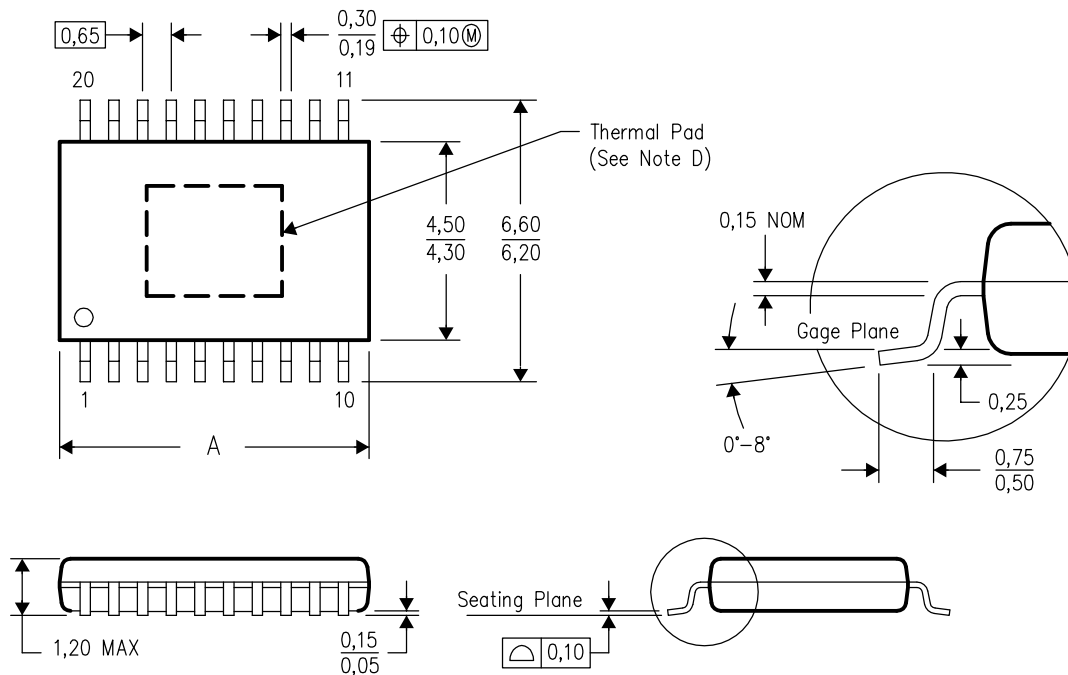
Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PWP (R-PDSO-G**)

PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE

20 PIN SHOWN

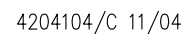


PINS **	14	16	20	24	28
DIM					
A MAX	5,10	5,10	6,60	7,90	9,80
A MIN	4,90	4,90	6,40	7,70	9,60

4073225/G 08/03

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusions.
 - This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <<http://www.ti.com>>.
 - Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.



**TEXAS
INSTRUMENTS**
www.ti.com

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments
Post Office Box 655303 Dallas, Texas 75265

Copyright © 2005, Texas Instruments Incorporated